MBRB8H100T4G, NBRB8H100T4G

Switch-mode Schottky Power Rectifier

Surface Mount Power Package

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured Not Sheared!
- AEC-Q101 Qualified and PPAP Capable
- NBRB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb-Free*

Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 1.7 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
 - Machine Model = C (> 400 V)
 - Human Body Model = 3B (> 8000 V)



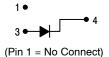
ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 8 AMPERES, 100 VOLTS



D²PAK CASE 418B



MARKING DIAGRAM



B8H100 = Specific Device Code A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRB8H100T4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NBRB8H100T4G	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBRB8H100T4G, NBRB8H100T4G

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	V
Average Rectified Forward Current (Rated V _R) T _C = 171°C	I _{F(AV)}	8	Α
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 171°C	I _{FRM}	16	Α
Max Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz, 25°C)	I _{FSM}	250	Α
Operating Junction and Storage Temperature Range (Note 1)	T _J , T _{stg}	-65 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case (Note 2) Junction-to-Ambient	$egin{array}{c} {\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}} \end{array}$	1.1 44	°C/W

^{2.} When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) ($I_F = 8 \text{ A}, T_J = 25^{\circ}\text{C}$) ($I_F = 8 \text{ A}, T_J = 125^{\circ}\text{C}$)	V _F	0.71 0.55	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, $T_J = 25^{\circ}\text{C}$) (Rated dc Voltage, $T_J = 125^{\circ}\text{C}$)	I _R	4.5 5.3	μA mA

DYNAMIC CHARACTERISTICS (Per Leg)

Capacitance			pF
(V _R = 4.0 V, T _C = 25°C, Frequency = 1.0 MHz)		600	

^{3.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

MBRB8H100T4G, NBRB8H100T4G

TYPICAL CHARACTERISTICS

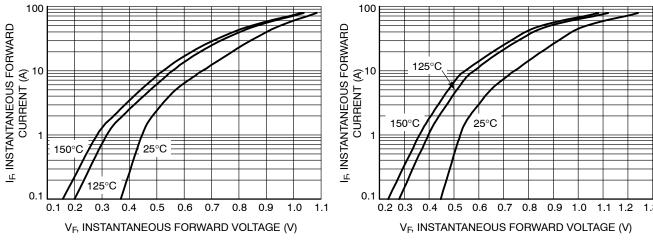


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

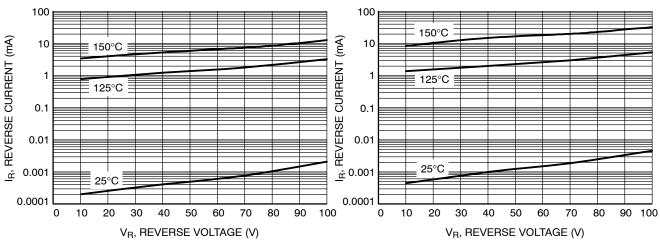


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

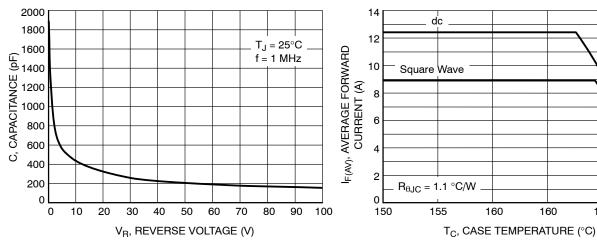


Figure 5. Typical Capacitance

Figure 6. Current Derating, Case

175

MBRB8H100T4G, NBRB8H100T4G

TYPICAL CHARACTERISTICS

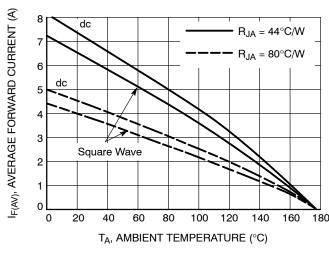


Figure 7. Current Derating, Ambient

Figure 8. Typical Forward Power Dissipation

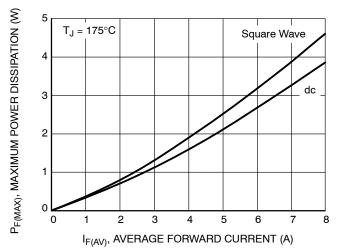


Figure 9. Maximum Forward Power Dissipation

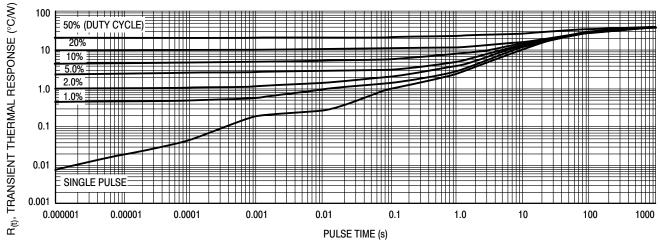


Figure 10. Thermal Response, Junction-to-Ambient

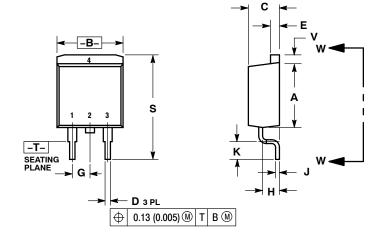




D²PAK 3 CASE 418B-04 ISSUE L

DATE 17 FEB 2015

SCALE 1:1



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTROLLING DIMENSION: INCH.
 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13

0.039 REF 0.99 REF 0.575 0.625 14.60 15.88

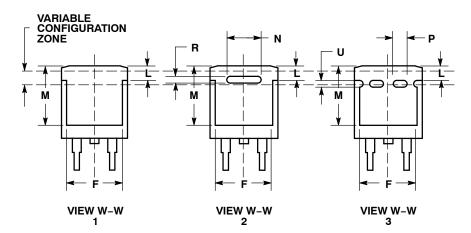
V 0.045 0.055 1.14 1.40

2.00 REF

0.197 REF

0.079 REF

R



STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4: PIN 1. GATE E 2. COLLECTOR

2. COLLECTOR 3. EMITTER 4. COLLECTOR STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

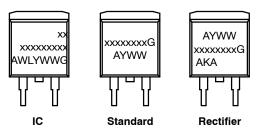
MARKING INFORMATION AND FOOTPRINT ON PAGE 2

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D ² PAK 3		PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*

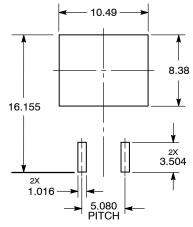


xx = Specific Device Code A = Assembly Location

WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D ² PAK 3		PAGE 2 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales